



STGB7NB60HD

N-CHANNEL 7A - 600V DPAK PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _C
STGB7NB60HD	600 V	< 2.8 V	7 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{cesat})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- OFF LOSSES INCLUDE TAIL CURRENT
- CO-PACKAGED WITH TURBOSWITCH™ ANTIPARALLEL DIODE
- SURFACE-MOUNTING D²PAK (TO-263) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "H" identifies a family optimized to achieve very low switching times for high frequency applications (<120kHz).

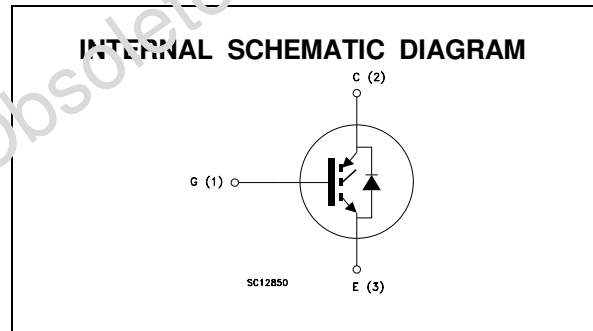
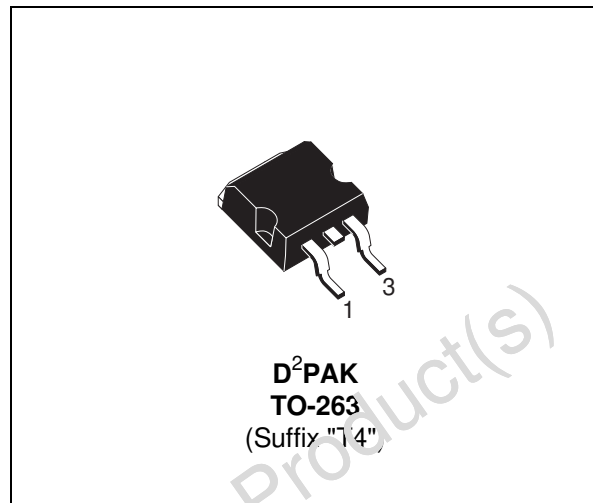
APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _c = 25 °C	14	A
I _C	Collector Current (continuous) at T _c = 100 °C	7	A
I _{CM} (•)	Collector Current (pulsed)	56	A
P _{tot}	Total Dissipation at T _c = 25 °C	80	W
	Derating Factor	0.64	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area



STGB7NB60HD

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.5	°C/W

ELECTRICAL CHARACTERISTICS (T_j = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CE)}	Collector-Emitter Breakdown Voltage	I _C = 250 μA V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating T _j = 25 °C V _{CE} = Max Rating T _j = 125 °C			250 2000	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V V _{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} I _C = 250 μA	3		5	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} = 15 V I _C = 7 A V _{GE} = 15 V I _C = 7 A T _j = 125 °C		2.3 1.9	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V I _C = 7 A	3.5	5		S
C _{ies} C _{oes} C _{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{CE} = 25 V f = 1 MHz V _{GE} = 0	390 45 10	560 68 15	730 90 20	pF pF pF
Q _G Q _{GE} Q _{GC}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V _{CE} = 480 V I _C = 7 A V _{GE} = 15 V		42 7.9 17.6	55	nC nC nC
I _{CL}	Latching Current	V _{clamp} = 480 V R _G = 10 Ω T _j = 150 °C	28			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Delay Time Rise Time	V _{CC} = 480 V I _C = 7 A V _{GE} = 15 V R _G = 10 Ω		15 48		ns ns
(di/dt) _{on}	Turn-on Current Slope	V _{CC} = 480 V I _C = 7 A R _G = 10 Ω V _{GE} = 15 V		160		A/μs
E _{on(○)}	Turn-on Switching Losses	T _j = 125 °C		185		μJ

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING OFF

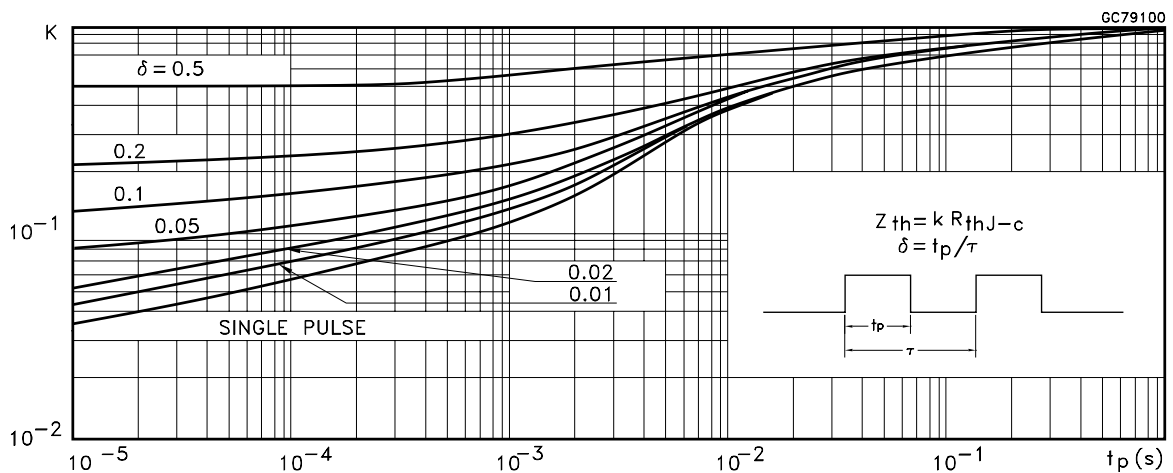
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-Over Time	VCC = 480 V R _{GE} = 10 Ω I _C = 7 A V _{GE} = 15 V		85		ns
$t_r(v_{off})$	Off Voltage Rise Time			20		ns
$t_d(off)$	Delay Time			75		ns
t_f	Fall Time			70		ns
$E_{off(**)}$	Turn-off Switching Loss				85	
$E_{ts(○)}$	Total Switching Loss			235		μJ
t_c	Cross-Over Time	VCC = 480 V R _{GE} = 10 Ω T _j = 125 °C I _C = 7 A V _{GE} = 15 V		150		ns
$t_r(v_{off})$	Off Voltage Rise Time			50		ns
$t_d(off)$	Delay Time			110		ns
t_f	Fall Time			110		ns
$E_{off(**)}$	Turn-off Switching Loss				220	
$E_{ts(○)}$	Total Switching Loss			405		μJ

COLLECTOR-EMITTER DIODE

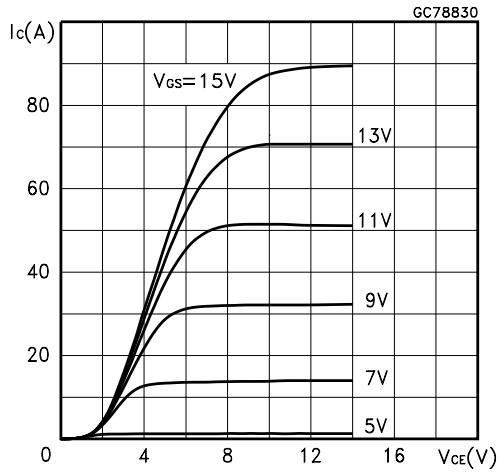
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f	Forward Current				7	A
I_{fm}	Forward Current pulsed				56	A
V_f	Forward On-Voltage	I _f = 7 A I _f = 7 A T _j = 125 °C		1.6 1.4	2.0	V V
t_{rr}	Reverse Recovery Time	I _f = 7 A dI/dt = 100 A/μS V _R = 200 V T _j = 125 °C		100		ns
Q_{rr}	Reverse Recovery Charge			180		nC
I_{rrm}	Reverse Recovery Current			3.6		A

- (●) Pulse width limited by max. junction temperature
- (○) Include recovery losses on the STTA506 freewheeling diode
- (*) Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
- (**) Losses Include Also The Tail (Jedec Standardization)

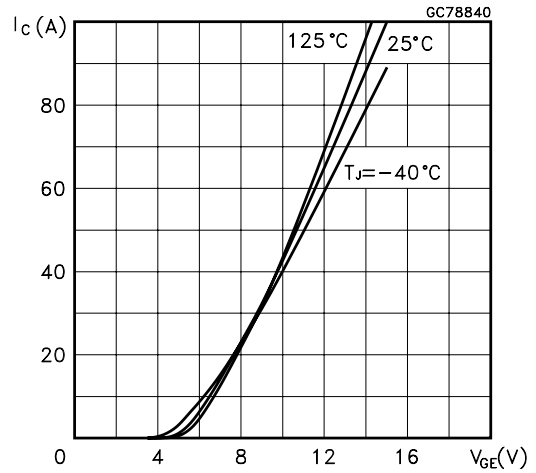
Thermal Impedance



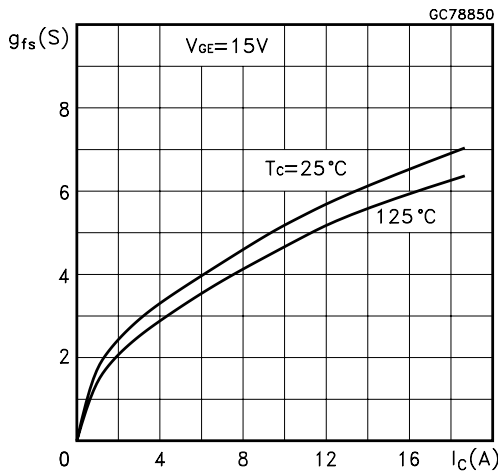
Output Characteristics



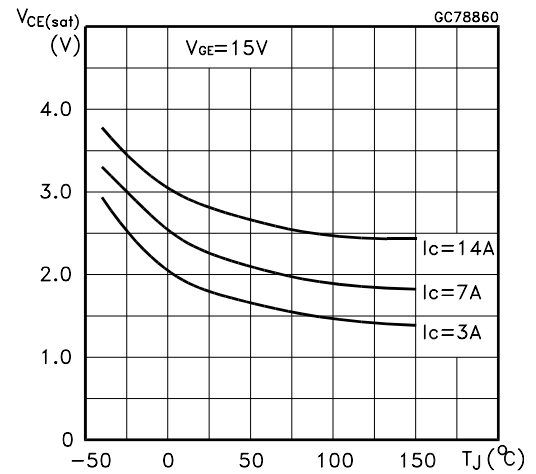
Transfer Characteristics



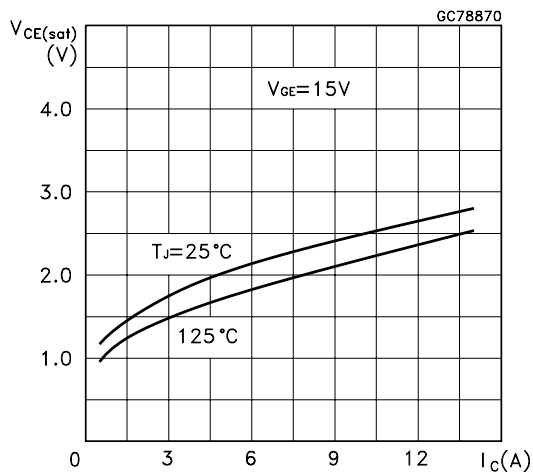
Transconductance



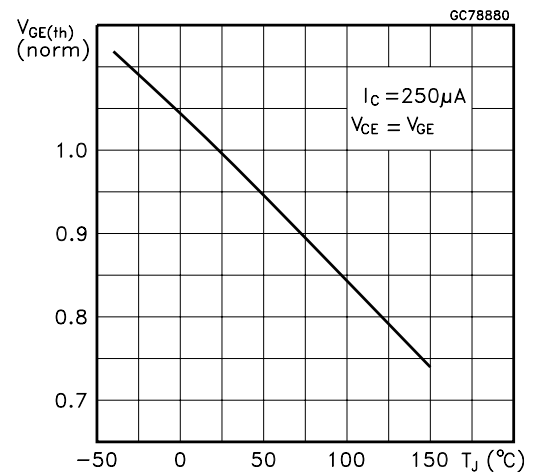
Collector-Emitter On Voltage vs Temperature



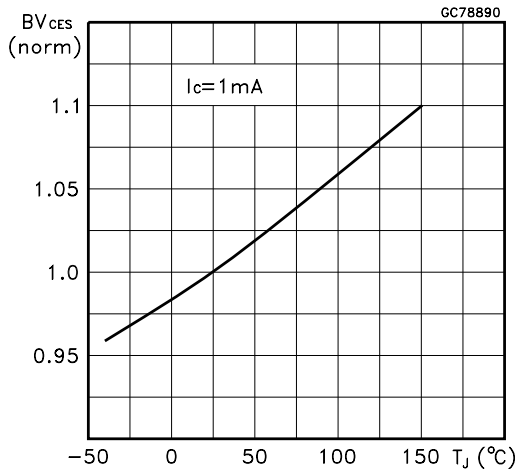
Collector-Emitter On Voltage vs Collector Current



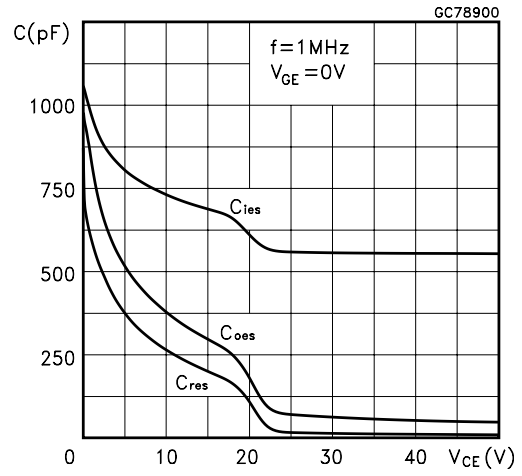
Gate Threshold vs Temperature



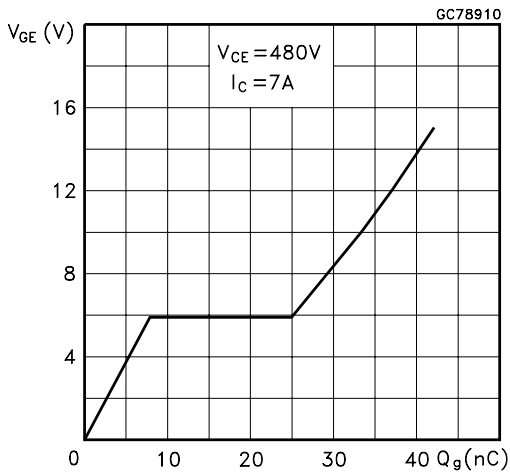
Normalized Breakdown Voltage vs Temperature



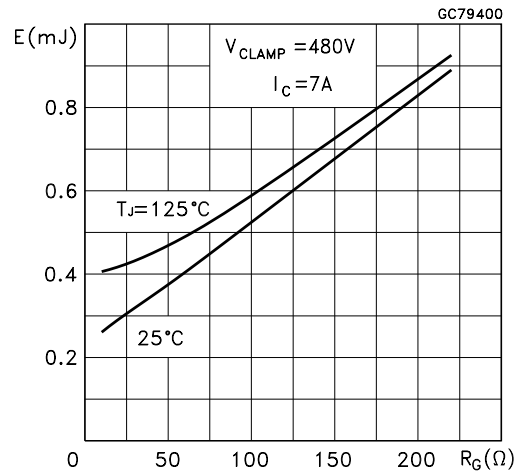
Capacitance Variations



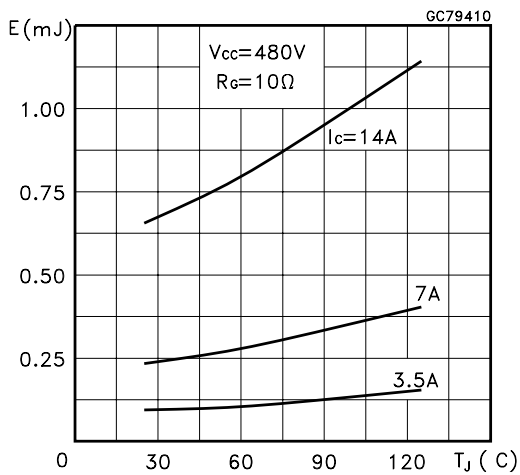
Gate Charge vs Gate-Emitter Voltage



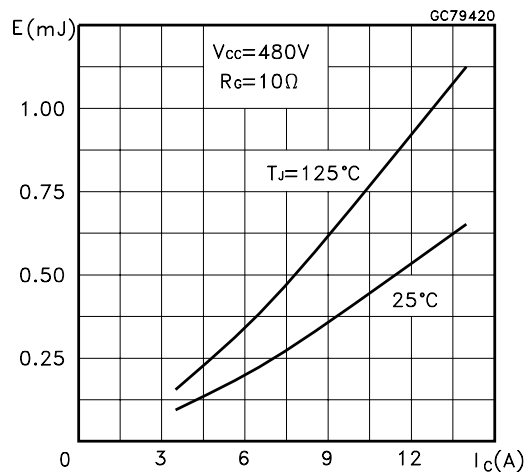
Total Switching Losses vs Gate Resistance



Total Switching Losses vs Temperature



Total Switching Losses vs Collector Current



Switching Off Safe Operating Area

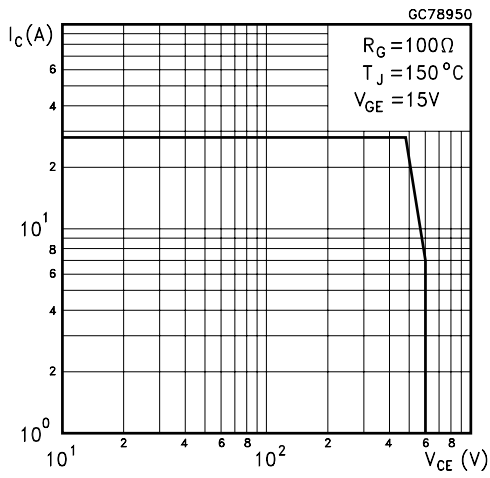


Fig. 1: Gate Charge test Circuit

Diode Forward Voltage

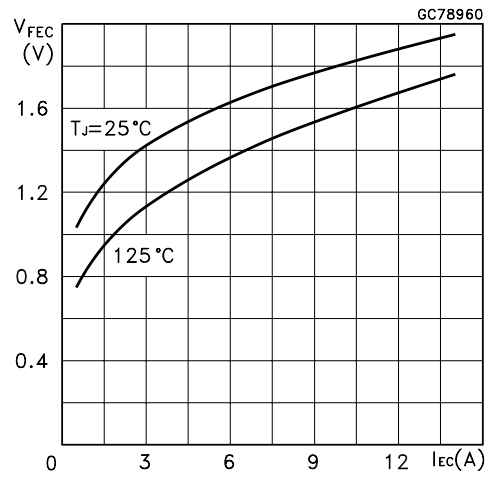


Fig. 2: Test Circuit For Inductive Load Switching

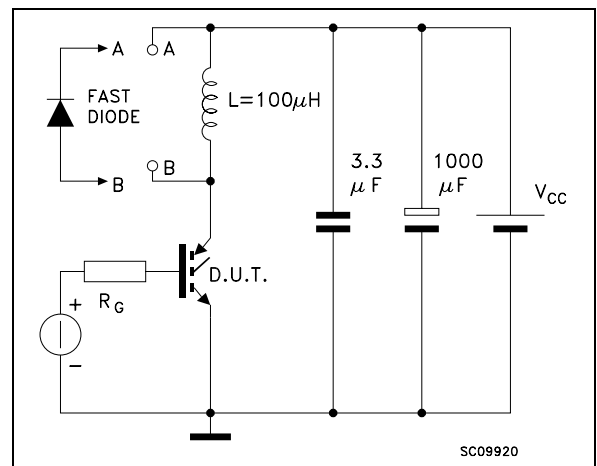
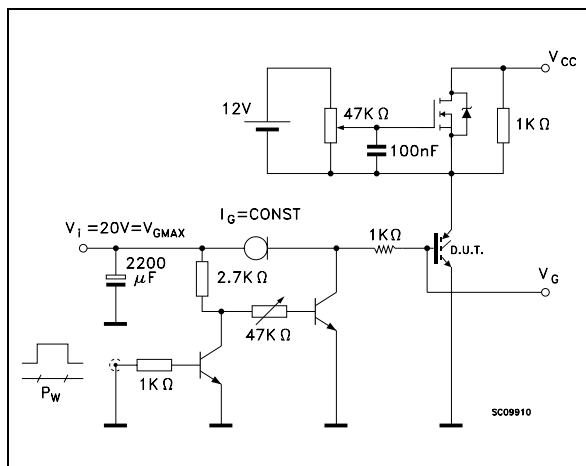
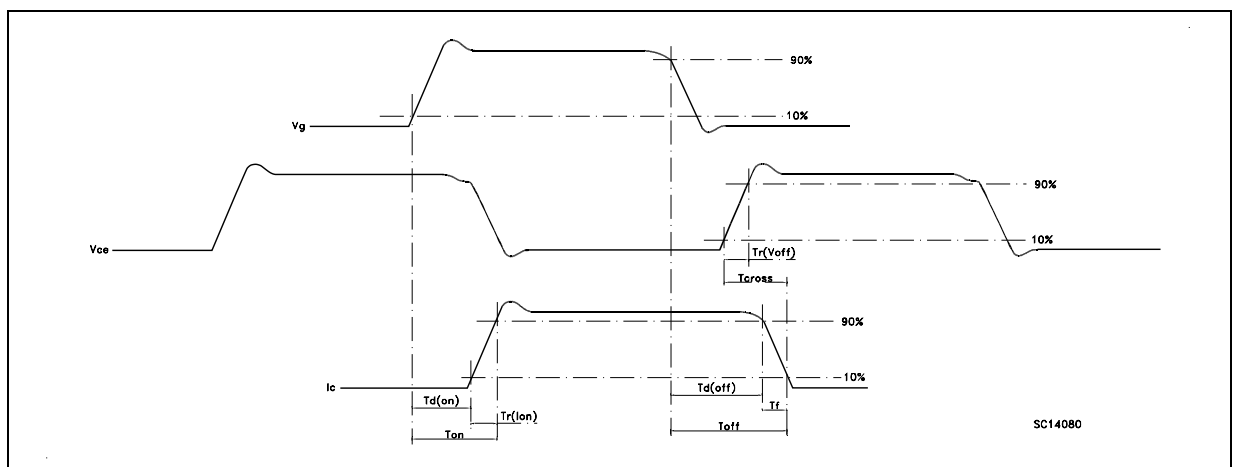
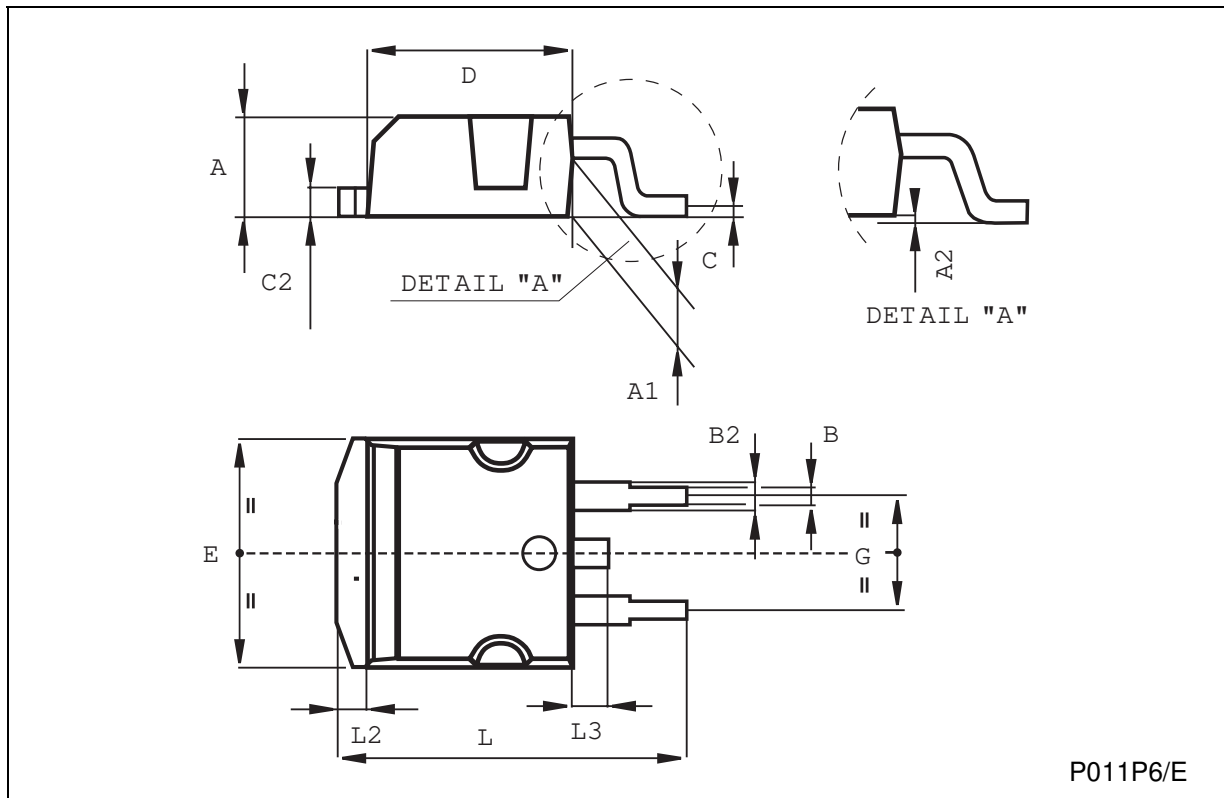


Fig. 3: Switching Waveforms



TO-263 (D²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.4	0.393		0.409
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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